NS2029M3

PNP Silicon General Purpose Amplifier Transistor

This PNP transistor is designed for general purpose amplifier applications. This device is housed in the SOT−723 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Reduces Board Space
- High h_{FE}, 210−460 (Typical)
- Low $V_{CE(sat)}$, < 0.5 V
- ESD Performance: Human Body Model; > 2000 V, Machine Model; > 200 V
- Available in 8000 Unit Tape & Reel with 2 mm Pitch
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Value	Unit
Collector−Base Voltage	$V_{(BR)CBO}$	−60	Vdc
Collector−Emitter Voltage	$V_{(BR)CEO}$	−50	Vdc
Emitter−Base Voltage	$V_{(BR)EBO}$	−6.0	Vdc
Collector Current − Continuous	I_C	−150	mAdc

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	P_D	265	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	−55 ~ +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Device mounted on a FR−4 glass epoxy printed circuit board using the minimum recommended footprint.

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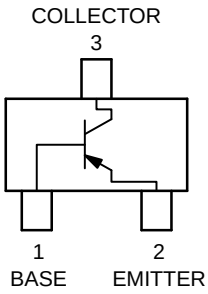
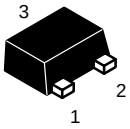
PNP GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT



MARKING DIAGRAM



SOT−723
CASE 631AA

9F = Specific Device Code
M = Date Code*

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NS2029M3T5G	SOT−723 (Pb−Free)	8000/Tape & Reel
NSV2029M3T5G	SOT−723 (Pb−Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector−Base Breakdown Voltage (I_C = −50 μAdc, I_E = 0)	$V_{(BR)CBO}$	−60	−	−	Vdc
Collector−Emitter Breakdown Voltage (I_C = −1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	−50	−	−	Vdc
Emitter−Base Breakdown Voltage (I_E = −50 μAdc, I_E = 0)	$V_{(BR)EBO}$	−6.0	−	−	Vdc
Collector−Base Cutoff Current (V_{CB} = −30 Vdc, I_E = 0)	I_{CBO}	−	−	−0.5	nA
Emitter−Base Cutoff Current (V_{EB} = −7.0 Vdc, I_B = 0)	I_{EBO}	−	−	−0.1	μA
Collector−Emitter Saturation Voltage (Note 2) (I_C = −50 mAdc, I_B = −5.0 mAdc)	$V_{CE(sat)}$	−	−	−0.5	Vdc
DC Current Gain (Note 2) (V_{CE} = −6.0 Vdc, I_C = −1.0 mAdc)	h_{FE}	120	−	560	−
Transition Frequency (V_{CE} = −12 Vdc, I_C = −2.0 mAdc, f = 30 MHz)	f_T	−	140	−	MHz
Output Capacitance (V_{CB} = −12 Vdc, I_E = 0 Adc, f = 1.0 MHz)	C_{OB}	−	3.5	−	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

TYPICAL ELECTRICAL CHARACTERISTICS

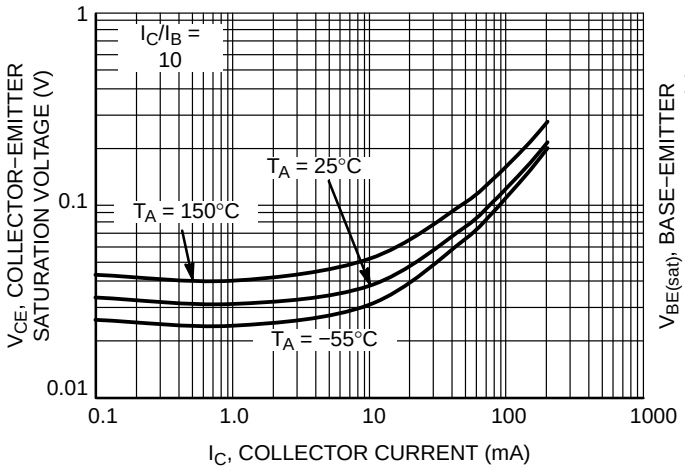


Figure 1. Collector−Emitter Saturation Voltage vs. Collector Current

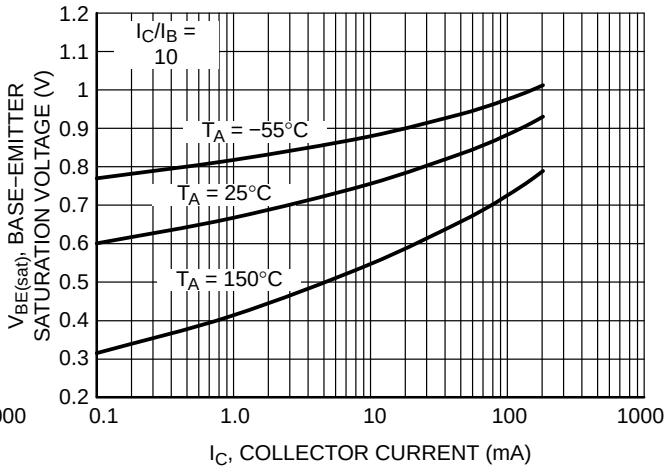


Figure 2. Base−Emitter Saturation Voltage vs. Collector Current

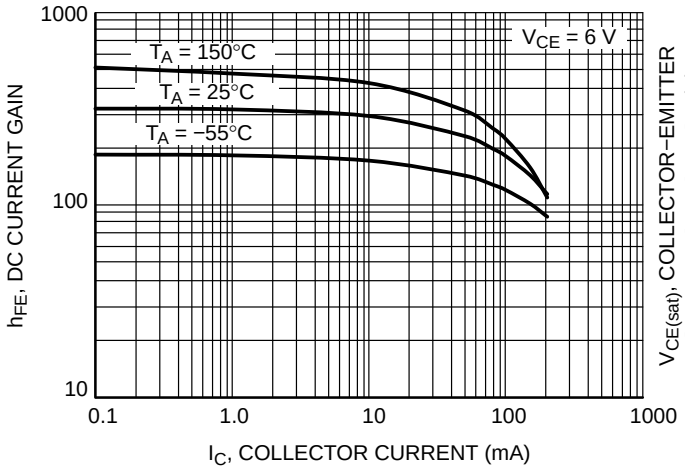


Figure 3. DC Current Gain vs. Collector Current

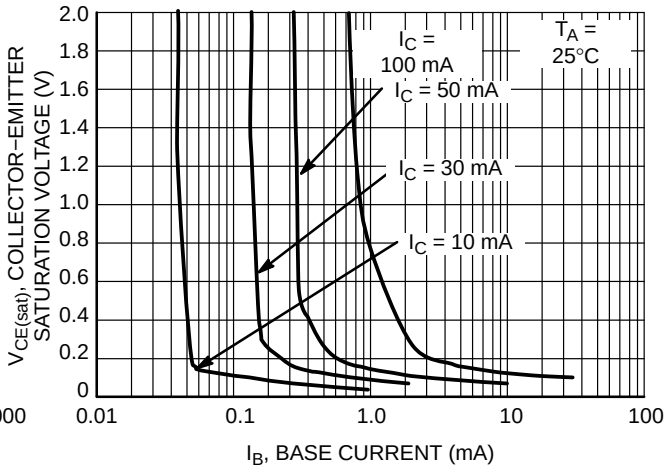


Figure 4. Saturation Region

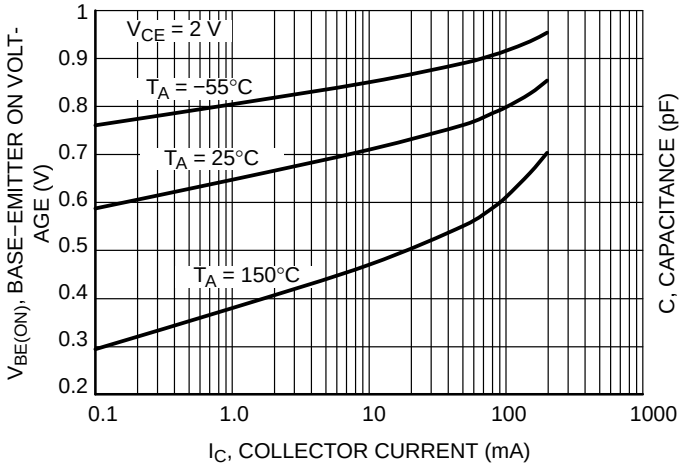


Figure 5. Base−Emitter Turn−ON Voltage vs. Collector Current

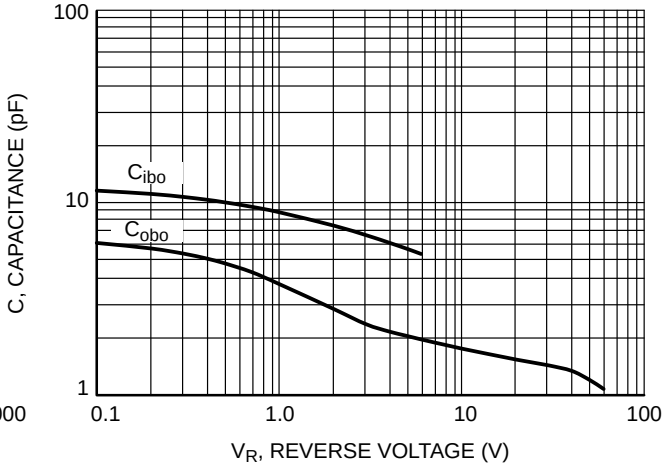


Figure 6. Capacitance

TYPICAL ELECTRICAL CHARACTERISTICS

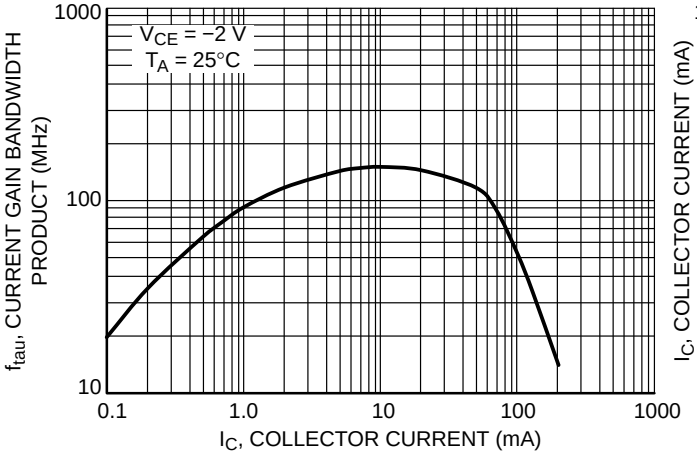


Figure 7. Current Gain Bandwidth Product vs. Collector Current

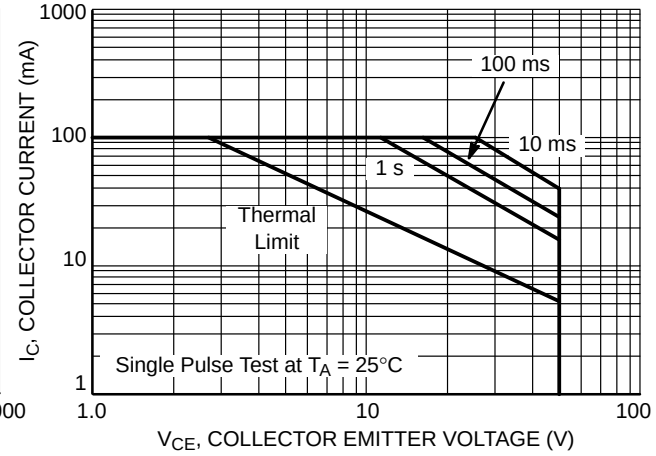
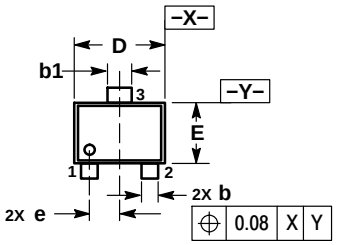


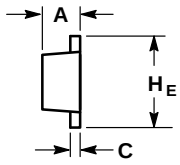
Figure 8. Safe Operating Area

PACKAGE DIMENSIONS

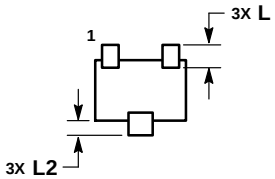
SOT−723
CASE 631AA
ISSUE D



TOP VIEW



SIDE VIEW

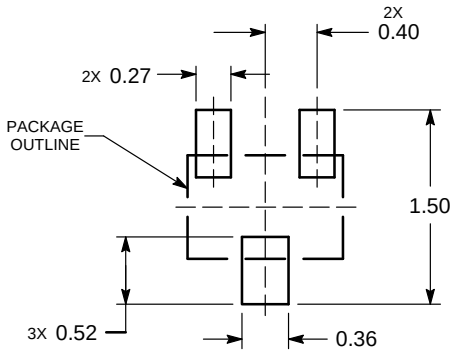


BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
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